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CORRECTION

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Correction: Synaptic plasticity and non-volatile memory characteristics in TiN-nanocrystal-embedded 3D vertical memristor-based synapses for neuromorphic systems

Seyeong Yang,^a Taegyun Kim,^a Sunghun Kim,^a Daewon Chung,^a Tae-Hyeon Kim,^d Jung Kyu Lee,^a Sungjoon Kim,^b Muhammad Ismail,^a Chandreswar Mahata,^a Sungjun Kim*^a and Seongjae Cho*^c

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^aDivision of Electronics and Electrical Engineering, Dongguk University, Seoul 04620, South Korea. E-mail: sungjun@dongguk.edu

^bDepartment of Electrical and Computer Engineering, Seoul National University, Seoul 08826, South Korea

^cDepartment of Electronic and Electrical Engineering, Ewha Womans University, Seoul 03760, South Korea. E-mail: felixcho@ewha.ac.kr

^dSchool of Electrical and Computer Engineering, Georgia Institute of Technology, Atlanta, GA, 30332, USA